

Amendments to the claims

Claims 1-20 (canceled)

Claim 21 (original): A method for making a semiconductor device comprising:

forming on a substrate a dielectric layer that has a dielectric constant that is greater than the dielectric constant of silicon dioxide;

forming a sacrificial layer on the dielectric layer;

removing the sacrificial layer; and then

forming a gate electrode on the dielectric layer.

Claims 22-37 (canceled)

Claim 38 (original): The method of claim 21 wherein the gate electrode is formed directly on the dielectric layer.

CERTIFICATE OF TRANSMISSION

(37 C.F.R. § 1.8(a))

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